

at least two connection sections that connect the signal line to the gate electrode layer, wherein at least one connection section is positioned outside of the element region and at least one connection section is positioned in the element region.

2. (amended) A driver circuit comprising a semiconductor integrated circuit having a plurality of transistors in which a single drive signal is applied to each of the transistors to drive the transistors to thereby drive a load, the driver circuit comprising:

- an element region at least partially surrounded by an element isolation region;
- a signal line for each of the transistors that supplies the drive signal and extends across the element region;
- a dielectric layer in the element region for each of the transistors;
- a gate electrode layer on the dielectric layer in the element region for each of the transistors, wherein part of the gate electrode layer extends to outside of the element region; and
- at least two connection sections that connect the signal line to the gate electrode for at least one of the transistors, wherein a first of the at least two connection sections is positioned outside of the element region and a second of the at least two connection sections is positioned in the element region.

Please add new claims 12-21 as follows:

12. (new) A driver circuit comprising a semiconductor integrated circuit having at least a first transistor in which a drive signal is applied to the first transistor, the driver circuit comprising:

- an isolation region extending around an active region of a semiconductor substrate;
- a dielectric layer on the active region;
- a first gate electrode layer of the first transistor formed on the dielectric layer on the active region;
- a first signal line that supplies the drive signal to the first transistor;
- a first connection extending from the first signal line to the gate electrode layer on the dielectric layer on the active region;

the first gate electrode layer also extending on the isolation region; and
a second connection extending from the signal line to the gate electrode layer on the
isolation region.

Cant
A2

12
13. (new) A driver circuit according to claim 11, wherein an additional dielectric
layer is positioned between the signal line and the first gate electrode layer, and the at least two
connections extend through the additional dielectric layer.

13
14. (new) A driver circuit according to claim 13, wherein the first transistor includes
source and drain regions positioned in the active region, and wherein a protective insulation layer
is formed in direct contact with the first gate electrode and the source and drain regions.

14
15. (new) A driver circuit according to claim 14, further comprising a silicide layer
formed in direct contact with the source and drain regions.

15
16. (new) A driver circuit according to claim 12 including a plurality of additional
transistors, the driver circuit further comprising:

a gate electrode layer on a dielectric layer on the active region for each of the additional
transistors;

a signal line for each of the additional transistors; and
at least one connection extending from the signal line for each of the additional transistors
to the gate electrode layer on the dielectric layer on the active region for each of the additional
transistors.

16
17. (new) A driver circuit according to claim 16,
wherein the gate electrode layer for each of the additional transistors also extends on the
isolation region; and

wherein at least one connection extends from the signal line for each of the additional
transistors to the gate electrode layer on the isolation region.



enix
17
18. (new) A driver circuit according to claim ~~17~~¹⁶, wherein at least two of the transistors have a different number of connections extending from the signal line to the gate electrode layer.

enix
18
19. (new) A driver circuit comprising a semiconductor integrated circuit having at least a first transistor in which a drive signal is applied to the first transistor, the driver circuit comprising:

an isolation region extending around an active region of the semiconductor substrate, the transistor including source and drain regions formed in the active region;

a dielectric layer formed on the substrate;

a first gate electrode layer of the first transistor formed on the dielectric layer on the semiconductor substrate and extending across the active region;

a first signal line that supplies the drive signal, the first signal line extending across the active region; and

at least two connections extending from the first signal line to the first gate electrode, wherein at least one of the connections is positioned directly over the active region.

19
20. (new) A driver circuit as in claim ~~20~~¹⁸, further comprising additional transistors, the driver circuit further comprising:

a gate electrode layer on a dielectric layer on the active region for each of the additional transistors;

a signal line for each of the additional transistors; and

at least one connection section extending from the signal line for each of the additional transistors to the gate electrode layer on the dielectric layer on the active region for each of the additional transistors.

20
21. (new) A driver circuit according to claim ~~20~~¹⁹, wherein at least two of the transistors have a different number of connections extending from the signal line to the gate electrode layer.--